



钜地半导体
Tudi Semiconductor

Product Specification

TUDI-TS1851/TS1852/TS1854

1.8 V input/output, rail-to-rail, low power operational amplifiers

网址 www.sztdbdt.com Q

用芯智造 · 卓越品质

**semiconductor device
manufacturer**

- Design
- research and development
- production
- and sales



Features

- Operating range from $V_{CC} = 1.8$ to 6 V
- Rail-to-rail input and output
- Extended V_{icm} ($V_{CC-} - 0.2\text{ V}$ to $V_{CC+} + 0.2\text{ V}$)
- Low supply current (120 A)
- Good accuracy (1 mV max for A version)
- Gain bandwidth product (530 kHz)
- High unity gain stability (able to drive 500 pF)
- ESD tolerance (2 kV)
- Latch-up immunity
- Available in SOT23-5 micropackage

Applications

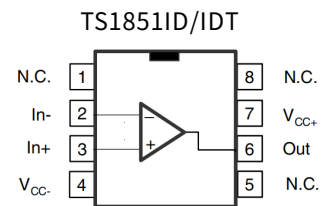
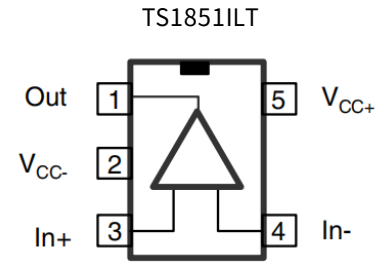
- Two-cell battery-powered systems
- Battery-powered electronic equipment
- Cordless phones
- Cellular phones
- Laptops
- PDAs

Description

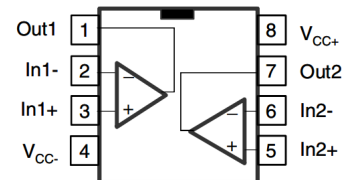
The TS185x (single, dual and quad) can operate with voltages as low as 1.8 V . They feature both input and output rail-to-rail (1.71 at $V_{CC} = 1.8\text{ V}$, $R_L = 2\text{ k}$), 120 A current consumption and 530 kHz gain bandwidth product.

With this low consumption and a sufficient GBP for many applications, these operational amplifiers are well-suited to all kinds of battery supplied and portable applications.

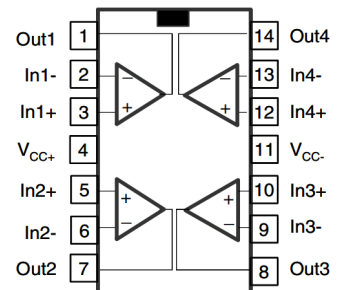
The TS1851 is housed in the space-saving 5-pin SOT23-5 package, which simplifies board design (outside dimensions are $2.8\text{ mm} \times 2.9\text{ mm}$).



TS1852ID/IDT-TS1852IST-TS1852IPT



TS1854ID/IDT-TS1854IPT





2 Electrical characteristics

Table 4. Electrical characteristics measured at $V_{CC+} = +1.8\text{ V}$, $V_{CC-} = 0\text{ V}$, with C_L and R_L connected to $V_{CC}/2$, $T_{amb} = 25^\circ\text{C}$ (unless otherwise specified) ⁽¹⁾

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{io}	Input offset voltage	TS1851/2/4 $T_{min} \leq T_{amb} \leq T_{max}$ TS1851A/2A/4A $T_{min} \leq T_{amb} \leq T_{max}$		0.1	3 6 1 1.5	mV
ΔV_{io}	Input offset voltage drift			2		$\mu\text{V}/^\circ\text{C}$
I_{io}	Input offset current	$V_{icm} = V_{out} = V_{CC}/2$ ⁽²⁾ $T_{min} \leq T_{amb} \leq T_{max}$		1	9 25	nA
I_{ib}	Input bias current	$V_{icm} = V_{out} = V_{CC}/2$ ⁽²⁾ $T_{min} \leq T_{amb} \leq T_{max}$		10	50 80	nA
CMR	Common mode rejection ratio $20 \log (\Delta V_{ic}/\Delta V_{io})$	$0 \leq V_{icm} \leq V_{CC}$ $T_{min} \leq T_{amb} \leq T_{max}$	55 52	85		dB
A_{vd}	Large signal voltage gain	$V_{out} = 0.5\text{ to }1.3\text{ V}$ $R_L = 10\text{ k}\Omega$ $R_L = 2\text{ k}\Omega$	80 70	100 100		dB
V_{OH}	High level output voltage	$V_{id} = 100\text{ mV}$ $R_L = 10\text{ k}\Omega$ $R_L = 2\text{ k}\Omega$ $T_{min} \leq T_{amb} \leq T_{max}$, $R_L = 10\text{ k}\Omega$ $T_{min} \leq T_{amb} \leq T_{max}$, $R_L = 2\text{ k}\Omega$	1.7 1.65 1.7 1.65	1.77 1.7		V
V_{OL}	Low level output voltage	$V_{id} = -100\text{ mV}$ $R_L = 10\text{ k}\Omega$ $R_L = 2\text{ k}\Omega$ $T_{min} \leq T_{amb} \leq T_{max}$, $R_L = 10\text{ k}\Omega$ $T_{min} \leq T_{amb} \leq T_{max}$, $R_L = 2\text{ k}\Omega$		40 62	70 90 100 120	mV
I_o	Output source current	$V_{id} = 100\text{ mV}$, $V_O = V_{CC-}$ at T_{amb}	15	29		mA
		at $T_{min} \leq T_{amb} \leq T_{max}$	5	5		
	Output sink current	$V_{id} = -100\text{ mV}$, $V_O = V_{CC+}$, at T_{amb}	15	46		mA
		at $T_{min} \leq T_{amb} \leq T_{max}$	5			
I_{CC}	Supply current (per amplifier)	$V_{out} = V_{CC}/2$ $A_{VCL} = 1$, no load $T_{min} \leq T_{amb} \leq T_{max}$		120	170 200	μA
GBP	Gain bandwidth product	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$, $f = 100\text{ kHz}$	300	530		kHz
SR	Slew rate	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$, $A_V = 1$	0.1	0.18		$\text{V}/\mu\text{s}$
ϕ_m	Phase margin	$C_L = 100\text{ pF}$		60		Degrees
e_n	Input voltage noise	$f = 1\text{ kHz}$		40		$\text{nV}/\sqrt{\text{Hz}}$
THD	Total harmonic distortion			0.01		%

1. All parameter limits at temperatures other than 25°C are guaranteed by correlation.
2. Maximum values include unavoidable inaccuracies of the industrial tests.



Table 5. Electrical characteristics measured at $V_{CC+} = +3\text{ V}$, $V_{CC-} = 0\text{ V}$, with C_L and R_L connected to $V_{CC}/2$, $T_{\text{amb}} = 25^\circ\text{C}$ (unless otherwise specified) ⁽¹⁾

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{io}	Input offset voltage	$V_{icm} = V_{out} = V_{CC}/2$ TS1851/2/4 $T_{\min} \leq T_{\text{amb}} \leq T_{\max}$ TS1851A/2A/4A $T_{\min} \leq T_{\text{amb}} \leq T_{\max}$		0.1	3 6 1 1.5	mV
ΔV_{io}	Input offset voltage drift			2		$\mu\text{V}/^\circ\text{C}$
I_{io}	Input offset current	$V_{icm} = V_{out} = V_{CC}/2^{(2)}$ $T_{\min} \leq T_{\text{amb}} \leq T_{\max}$		1	9 25	nA
I_{ib}	Input bias current	$V_{icm} = V_{out} = V_{CC}/2^{(2)}$ $T_{\min} \leq T_{\text{amb}} \leq T_{\max}$		10	55 85	nA
CMR	Common mode rejection ratio $20 \log (\Delta V_{ic}/\Delta V_{io})$	$0 \leq V_{icm} \leq V_{CC}$ $T_{\min} \leq T_{\text{amb}} \leq T_{\max}$	60 57	90		dB
A_{vd}	Large signal voltage gain	$V_{out} = 0.5 \text{ to } 2.5\text{ V}$ $R_L = 10\text{ k}\Omega$ $R_L = 2\text{ k}\Omega$	83 74	102 102		dB
V_{OH}	High level output voltage	$V_{id} = 100\text{ mV}$ $R_L = 10\text{ k}\Omega$ $R_L = 2\text{ k}\Omega$ $T_{\min} \leq T_{\text{amb}} \leq T_{\max}$, $R_L = 10\text{ k}\Omega$ $T_{\min} \leq T_{\text{amb}} \leq T_{\max}$, $R_L = 2\text{ k}\Omega$	2.9 2.85 2.9 2.85	2.96 2.94		V
V_{OL}	Low level output voltage	$V_{id} = -100\text{ mV}$ $R_L = 10\text{ k}\Omega$ $R_L = 2\text{ k}\Omega$ $T_{\min} \leq T_{\text{amb}} \leq T_{\max}$, $R_L = 10\text{ k}\Omega$ $T_{\min} \leq T_{\text{amb}} \leq T_{\max}$, $R_L = 2\text{ k}\Omega$		10 46	90 100 120 130	mV
I_o	Output source current	$V_{id} = 100\text{ mV}$, $V_O = V_{CC-}$, at T_{amb}	15	47		mA
		At $T_{\min} \leq T_{\text{amb}} \leq T_{\max}$	5			
	Output sink current	$V_{id} = -100\text{ mV}$, $V_O = V_{CC+}$, at T_{amb}	15	47		mA
		At $T_{\min} \leq T_{\text{amb}} \leq T_{\max}$	5			
I_{CC}	Supply current (per amplifier)	$V_{out} = V_{CC}/2$ $A_{VCL} = 1$, no load $T_{\min} \leq T_{\text{amb}} \leq T_{\max}$		150	200 230	μA
GBP	Gain bandwidth product	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$, $f = 100\text{ kHz}$	370	600		kHz
SR	Slew rate	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$, $A_V = 1$	0.12	0.2		$\text{V}/\mu\text{s}$
ϕ_m	Phase margin	$C_L = 100\text{ pF}$		60		Degrees
e_n	Input voltage noise	$f = 1\text{ kHz}$		40		$\text{nV}/\sqrt{\text{Hz}}$
THD	Total harmonic distortion	$V_{out} = 2 V_{pk-pk}$, $A_V = -1$, $f = 1\text{ kHz}$		0.005		%

1. All parameter limits at temperatures other than 25°C are guaranteed by correlation.

2. Maximum values include unavoidable inaccuracies of the industrial tests.



Table 6. Electrical characteristics measured at $V_{CC+} = +5\text{ V}$, $V_{CC-} = 0\text{ V}$, with C_L and R_L connected to $V_{CC}/2$, $T_{amb} = 25^\circ\text{C}$ (unless otherwise specified) ⁽¹⁾

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{io}	Input offset voltage	$V_{icm} = V_{out} = V_{CC}/2$ TS1851/2/4 $T_{min} \leq T_{amb} \leq T_{max}$ TS1851A/2A/4A $T_{min} \leq T_{amb} \leq T_{max}$		0.1	3 6 1 1.5	mV
ΔV_{io}	Input offset voltage drift			2		$\mu\text{V}/^\circ\text{C}$
I_{io}	Input offset current	$V_{icm} = V_{out} = V_{CC}/2^{(2)}$ $T_{min} \leq T_{amb} \leq T_{max}$		1	9 25	nA
I_{ib}	Input bias current	$V_{icm} = V_{out} = V_{CC}/2^{(2)}$ $T_{min} \leq T_{amb} \leq T_{max}$		16	63 93	nA
CMR	Common mode rejection ratio $20 \log (\Delta V_{ic}/\Delta V_{io})$	$0 \leq V_{icm} \leq V_{CC}$ $T_{min} \leq T_{amb} \leq T_{max}$	65 62	95		dB
SVR	Supply voltage rejection ratio $20 \log (\Delta V_{cc}/\Delta V_{io})$	$V_{CC} = 1.8 \text{ to } 5\text{ V}$	70	90		dB
A_{vd}	Large signal voltage gain	$V_{out} = 0.5 \text{ to } 4\text{ V}$ $R_L = 10\text{ k}\Omega$ $R_L = 2\text{ k}\Omega$	85 77	104 104		dB
V_{OH}	High level output voltage	$V_{id} = 100\text{ mV}$ $R_L = 10\text{ k}\Omega$ $R_L = 2\text{ k}\Omega$ $T_{min} \leq T_{amb} \leq T_{max}$, $R_L = 10\text{ k}\Omega$ $T_{min} \leq T_{amb} \leq T_{max}$, $R_L = 2\text{ k}\Omega$	4.85 4.8 4.85 4.8	4.95 4.91		V
V_{OL}	Low level output voltage	$V_{id} = -100\text{ mV}$ $R_L = 10\text{ k}\Omega$ $R_L = 2\text{ k}\Omega$ $T_{min} \leq T_{amb} \leq T_{max}$, $R_L = 10\text{ k}\Omega$ $T_{min} \leq T_{amb} \leq T_{max}$, $R_L = 2\text{ k}\Omega$		40 80	180 200 180 200	mV
I_o	Output source current	$V_{id} = 100\text{ mV}$, $V_O = V_{CC-}$, at T_{amb}	15	48		mA
		at $T_{min} \leq T_{amb} \leq T_{max}$	5			
	Output sink current	$V_{id} = -100\text{ mV}$, $V_O = V_{CC+}$, at T_{amb}	15	48		mA
		at $T_{min} \leq T_{amb} \leq T_{max}$	5			
I_{CC}	Supply current (per amplifier)	$V_{out} = V_{CC}/2$ $A_{VCL} = 1$, no load $T_{min} \leq T_{amb} \leq T_{max}$		162	220 250	μA
GBP	Gain bandwidth product	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$, $f = 100\text{ kHz}$	380	656		kHz
SR	Slew rate	$R_L = 10\text{ k}\Omega$, $C_L = 100\text{ pF}$, $A_V = 1$	0.13	0.25		V/ μs
ϕ_m	Phase margin	$C_L = 100\text{ pF}$		60		Degrees
e_n	Input voltage noise	$f = 1\text{ kHz}$		40		nV/ $\sqrt{\text{Hz}}$
THD	Total harmonic distortion	$V_{out} = 2 V_{pk-pk}$, $A_V = -1$, $f = 1\text{ kHz}$		0.01		%

1. All parameter limits at temperatures other than 25°C are guaranteed by correlation.
2. Maximum values include unavoidable inaccuracies of the industrial tests.

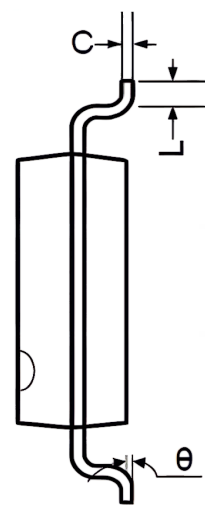
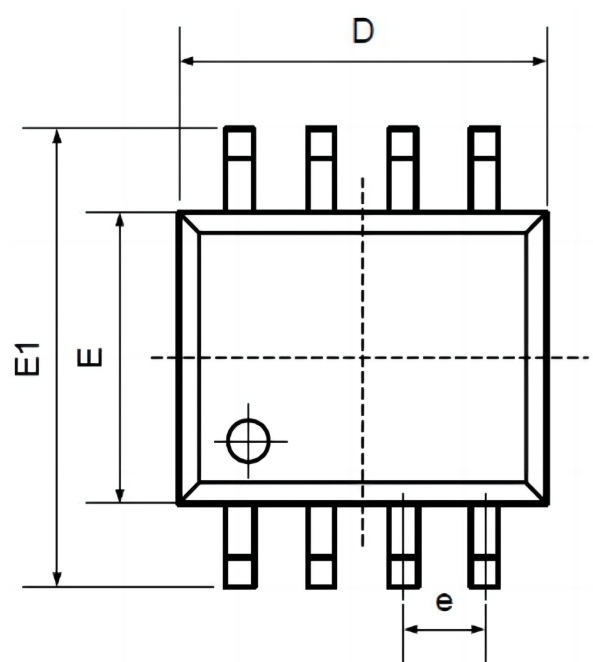


Order information

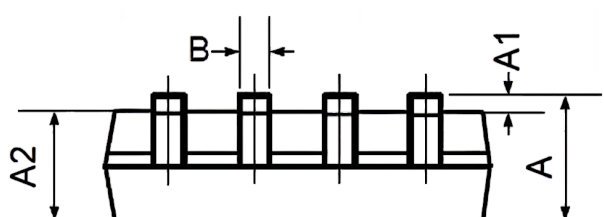
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TS1851IDT-TUDI	SOP8	Tape,Reel,2500	TS1851IDT
TS1851ILT-TUDI	SOT23	Tape,Reel,3000	TS1851ILT
TS1852AIDT-TUDI	SOP8	Tape,Reel,2500	TS1852AIDT
TS1852IDT-TUDI	SOP8	Tape,Reel,2500	TS1852IDT
TS1852IST-TUDI	MSOP8	Tape,Reel,2500	TS1852IST
TS1854AIDT-TUDI	SOP8	Tape,Reel,2500	TS1854AIDT
TS1854IDT-TUDI	SOP14	Tape,Reel,2500	TS1854IDT



Package SOP8

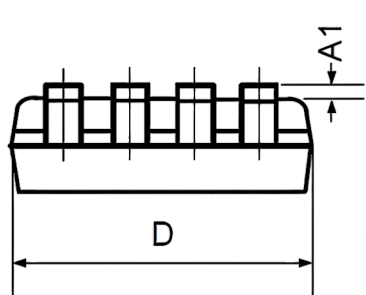
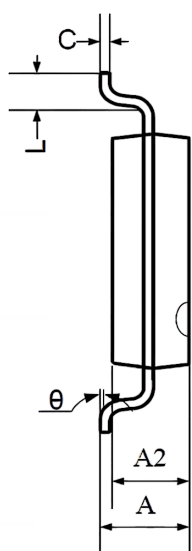
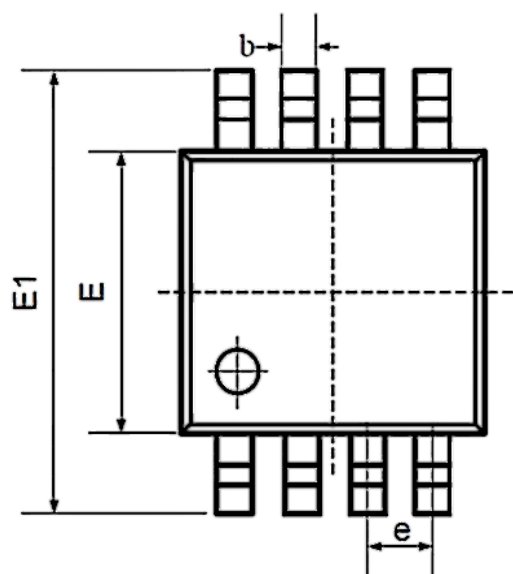


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
B	0.330	0.510	0.013	0.020
C	0.190	0.250	0.007	0.010
D	4.780	5.000	0.188	0.197
E	3.800	4.000	0.150	0.157
E1	5.800	6.300	0.228	0.248
e	1.270TYP		0.050TYP	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



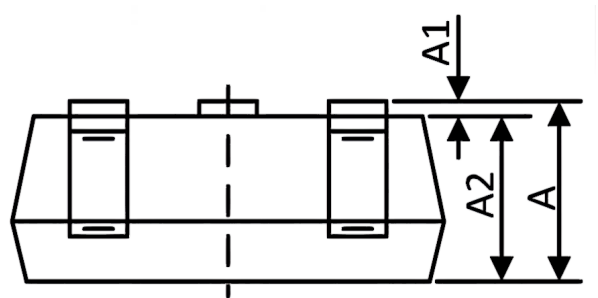
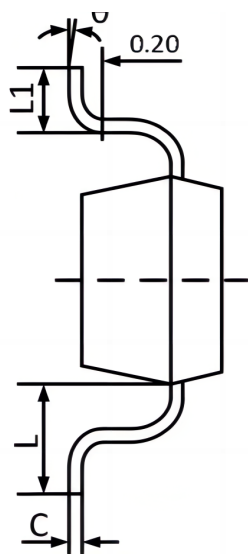
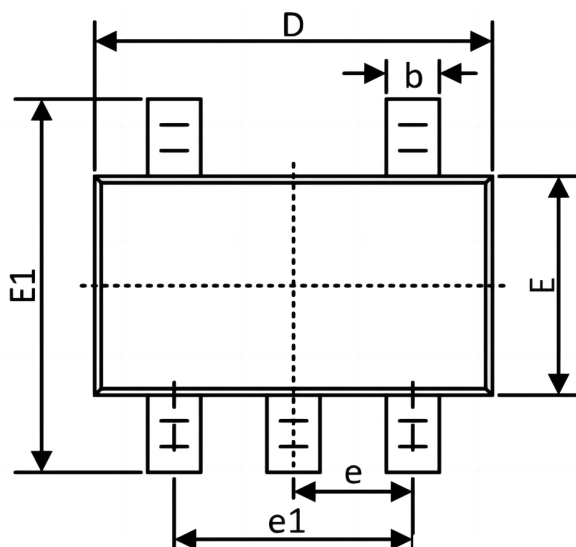


Package MSOP8



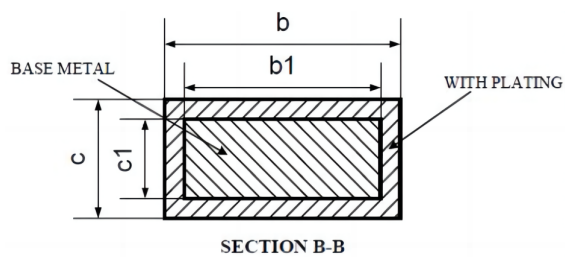
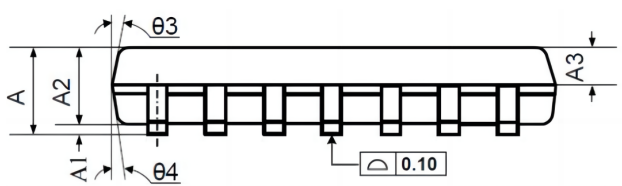
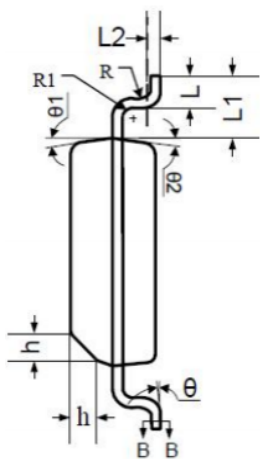
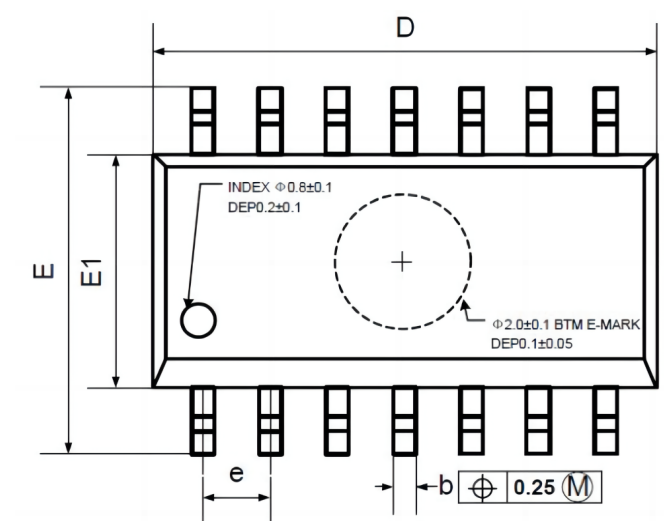
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.800	1.200	0.031	0.047
A1	0.000	0.200	0.000	0.008
A2	0.760	0.970	0.030	0.038
b	0.30 TYP		0.012 TYP	
C	0.15 TYP		0.006 TYP	
D	2.900	3.100	0.114	0.122
e	0.65 TYP		0.026 TYP	
E	2.900	3.100	0.114	0.122
E1	4.700	5.100	0.185	0.201
L	0.410	0.650	0.016	0.026
θ	0°	6°	0°	6°

Package SOT23-5



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.400	0.012	0.016
C	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.700REF		0.028REF	
L1	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

Package SOP14



Symbol	Dimensions In Millimeters		
	MIN	NOM	MAX
A	1.35	1.60	1.75
A1	0.10	0.15	0.25
A2	1.25	1.45	1.65
A3	0.55	0.65	0.75
b	0.36		0.49
b1	0.35	0.40	0.45
C	0.16		0.25
c1	0.15	0.20	0.25
D	8.53	8.63	8.73
E	5.80	6.00	6.20
E1	3.80	3.90	4.00
e	1.27 BSC		
L	0.45	0.60	0.80
L1	1.04 REF		
L2	0.25 BSC		
R	0.07		
R1	0.07		
h	0.30	0.40	0.50
θ	0°		8°
θ1	6°	8°	10°
θ2	6°	8°	10°
θ3	5°	7°	9°
θ4	5°	7°	9°



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